



**TECH PUBLIC**  
—台舟电子—

**TPM3134KW**  
20V P-Channel MOSFET

[www.sot23.com.tw](http://www.sot23.com.tw)

## Features

- Lead free
- Surface mount package
- P-Channel switch with low  $R_{DS(on)}$
- Operated at low logic level gate drive

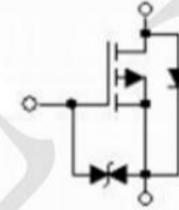
## Applications

- Load/Power switching
- Interfacing, logic switching
- Battery management for ultra small portable electronics

SOT323



Schematic Diagram



## Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	-20	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Continuous Drain Current <sup>1</sup>	$I_D$	-0.66	A
Pulsed Drain Current ( $t_p=10\mu\text{s}$ )	$I_{DM}$	-1.2	A
Power Dissipation <sup>1</sup>	$P_D$	150	mW
Thermal Resistance from Junction to Ambient <sup>1</sup>	$R_{\theta JA}$	833	$^\circ\text{C}/\text{W}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55 to +150	$^\circ\text{C}$
Lead Temperature for Soldering Purposes(1/8" from case for 10 S)	$T_L$	260	$^\circ\text{C}$



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### Electrical Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>STATIC CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = -250\mu\text{A}$	-20	-	-	V
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{\text{DS}} = -20\text{V}, V_{\text{GS}} = 0\text{V}$	-	-	-1	$\mu\text{A}$
Gate-Body Leakage Current	$I_{\text{GSS}}$	$V_{\text{GS}} = \pm 12\text{V}, V_{\text{DS}} = 0\text{V}$	-	-	20	$\mu\text{A}$
Gate Threshold Voltage <sup>2</sup>	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = -250\mu\text{A}$	-0.35	-	-1.1	V
Drain-Source On-Resistance <sup>2</sup>	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}} = -4.5\text{V}, I_D = -1\text{A}$	-	-	520	$\text{m}\Omega$
		$V_{\text{GS}} = -2.5\text{V}, I_D = -0.8\text{A}$	-	-	700	$\text{m}\Omega$
		$V_{\text{GS}} = -1.8\text{V}, I_D = -0.5\text{A}$	-	-	950	$\text{m}\Omega$
Forward Transconductance <sup>2</sup>	$g_{\text{FS}}$	$V_{\text{DS}} = -10\text{V}, I_D = -0.54\text{A}$	-	1.2	-	S
Diode Forward Voltage	$V_{\text{SD}}$	$I_S = -0.5\text{A}, V_{\text{GS}} = 0\text{V}$	-	-	-1.2	V
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}} = -16\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$	-	113	170	pF
Output Capacitance	$C_{\text{oss}}$		-	15	25	pF
Reverse Transfer Capacitance	$C_{\text{rss}}$		-	9	15	pF
<b>SWITCHING CHARACTERISTICS</b>						
Turn-on Delay Time <sup>3</sup>	$t_{\text{d}(\text{on})}$	$V_{\text{GS}} = -4.5\text{V}, V_{\text{DS}} = -10\text{V}, I_D = -200\text{mA}, R_{\text{GEN}} = 10\Omega$	-	9	-	nS
Turn-on Rise Time <sup>3</sup>	$t_r$		-	5.8	-	nS
Turn-off Delay Time <sup>3</sup>	$t_{\text{d}(\text{off})}$		-	32.7	-	nS
Turn-off Fall Time <sup>3</sup>	$t_f$		-	20.3	-	nS

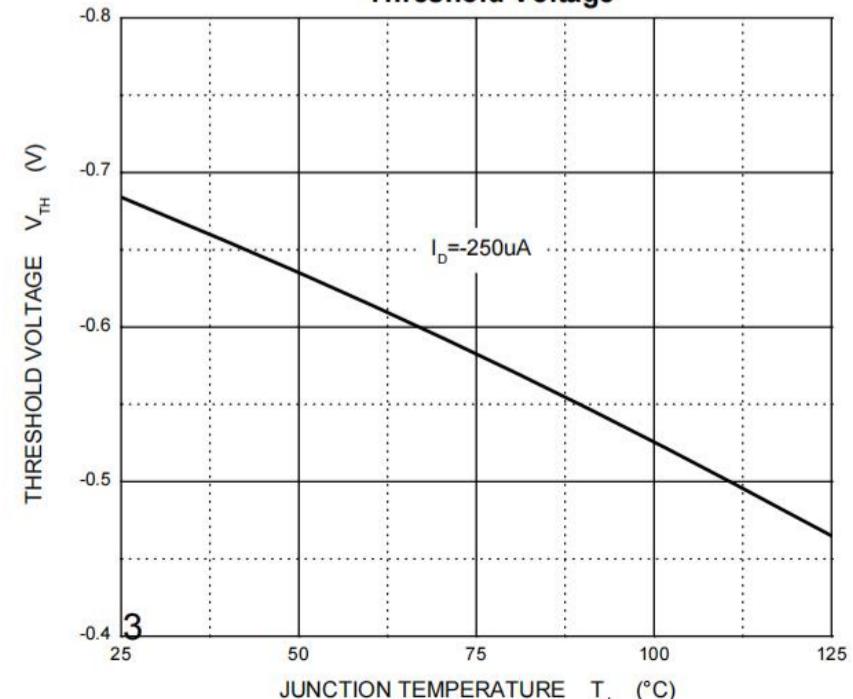
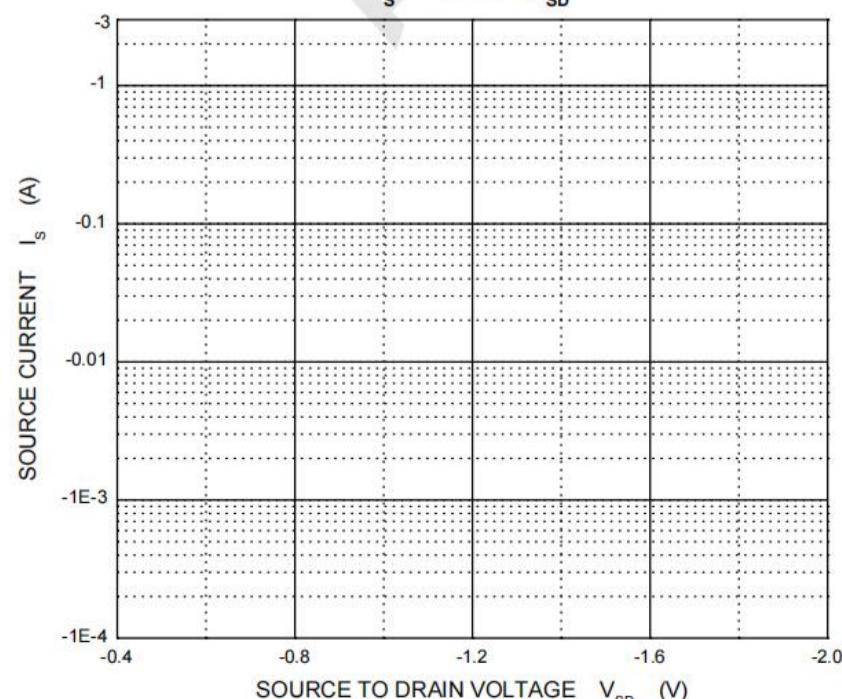
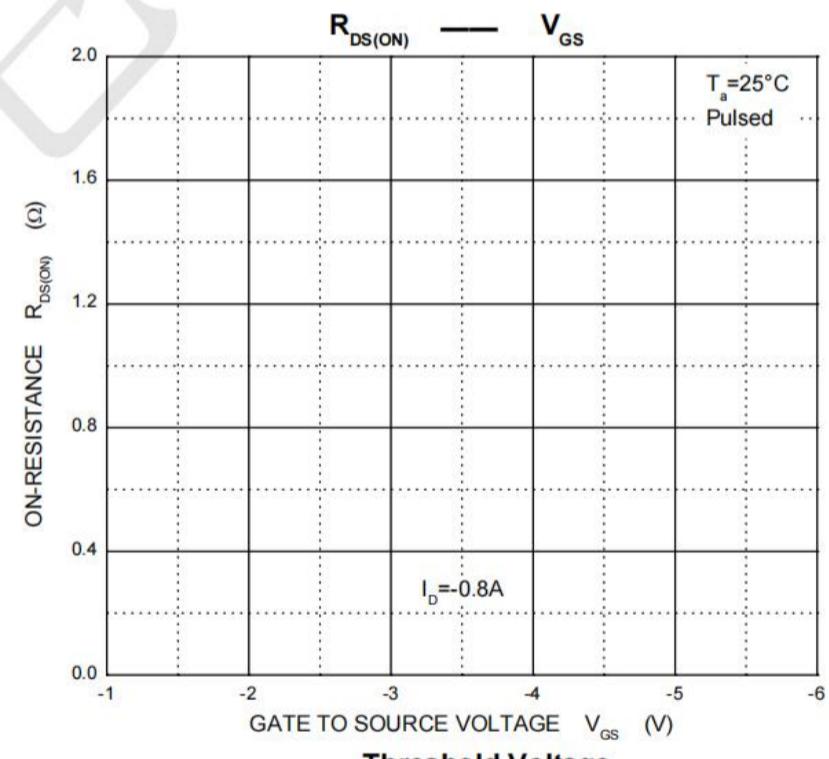
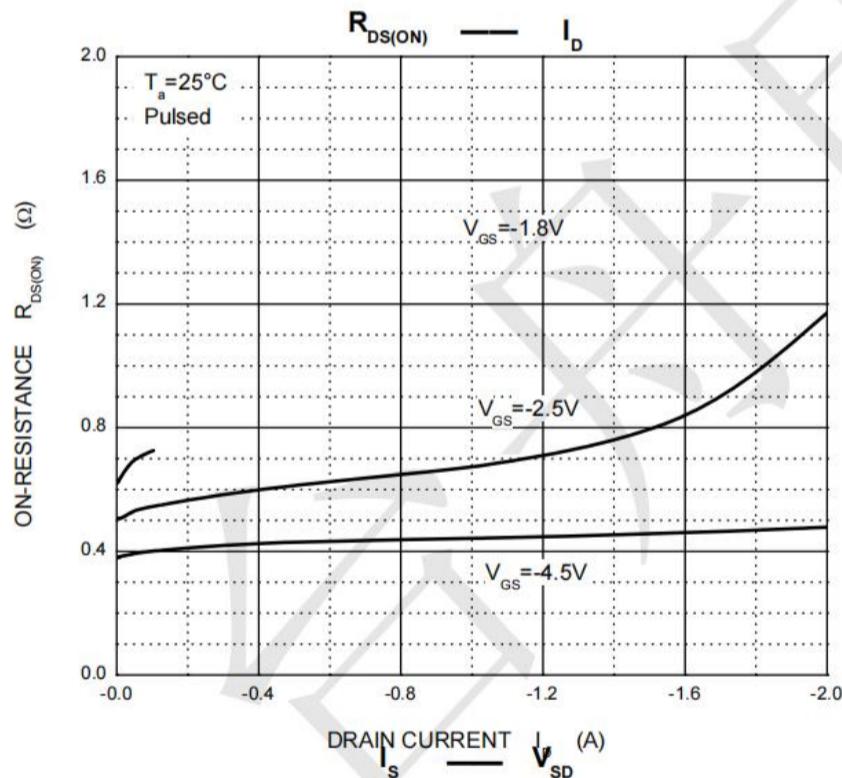
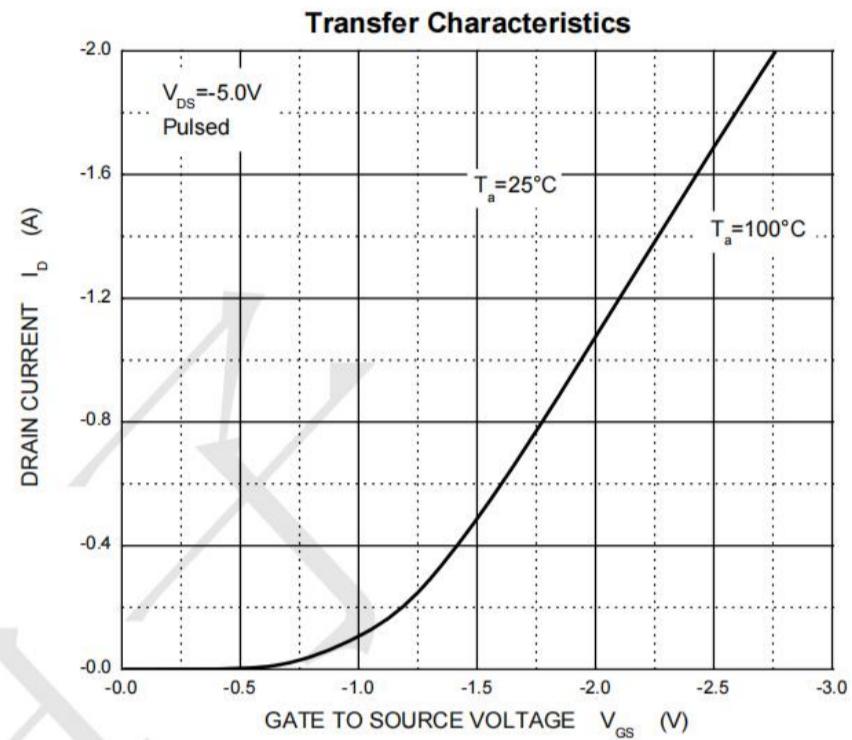
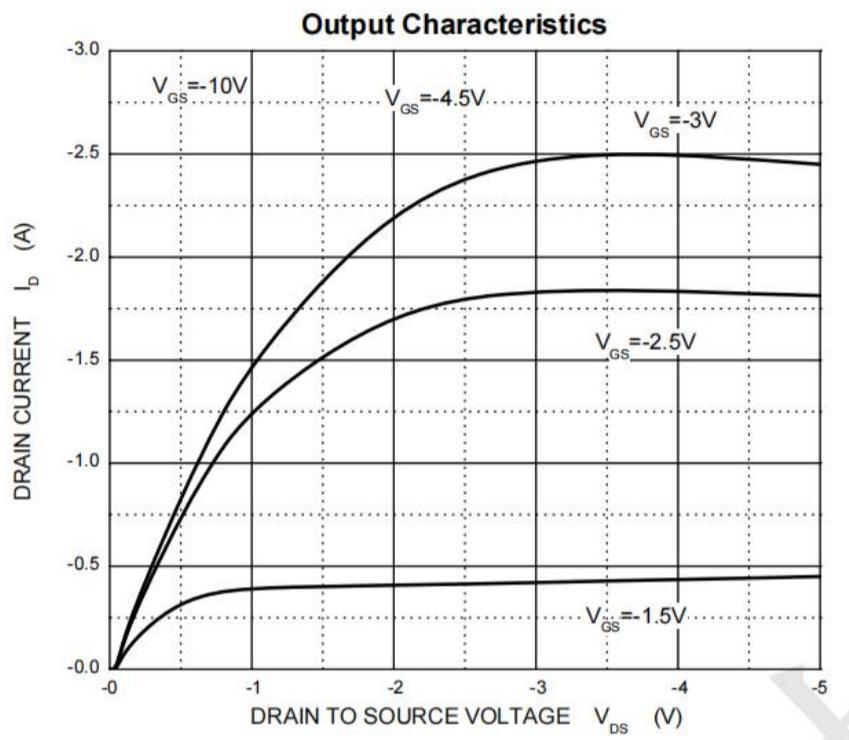


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## Typical Characteristics

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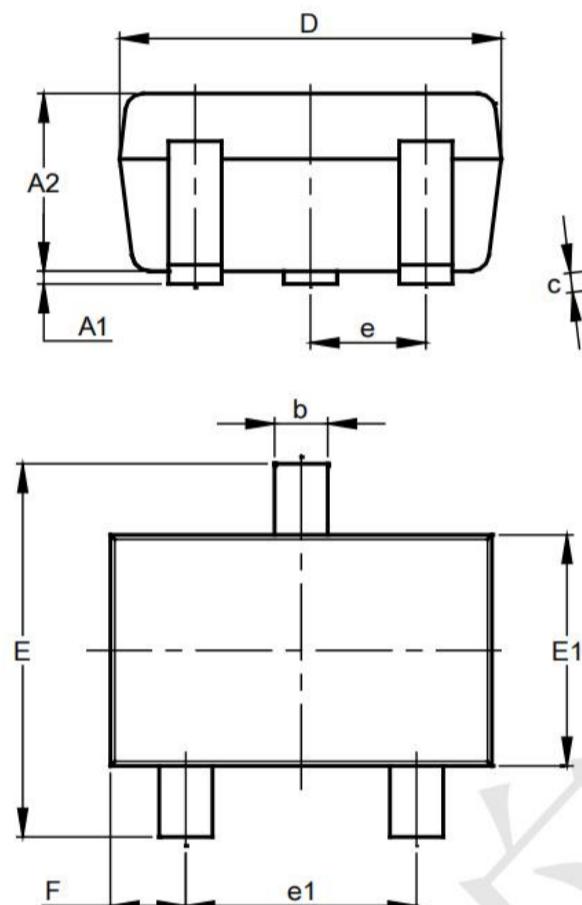


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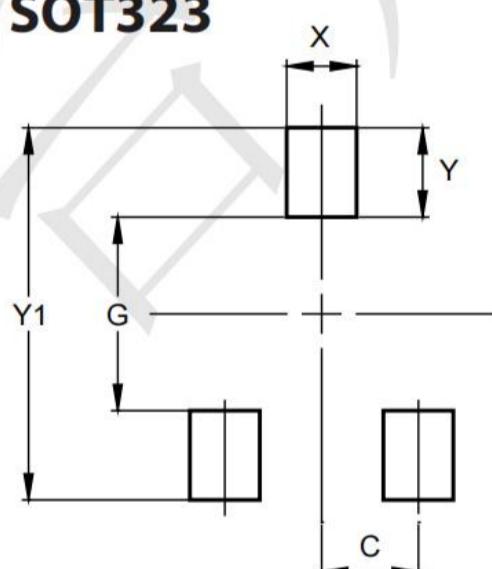
## Outline Drawing - SOT323(SC70-3)



SOT323			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.25	0.40	0.30
c	0.10	0.18	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
e1	1.20	1.40	1.30
F	0.375	0.475	0.425
L	0.25	0.40	0.30
a	0°	8°	--

All Dimensions in mm

## Land Pattern - SOT323



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500